

**08NM60**

Preliminary

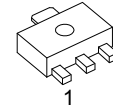
Power MOSFET**0.8A, 600V N-CHANNEL
SUPER-JUNCTION MOSFET****DESCRIPTION**

The UTC **08NM60** is an Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

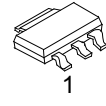
FEATURES

* $R_{DS(on)} \leq 4.5 \Omega$ @ $V_{GS}=10V$, $I_D=0.4A$

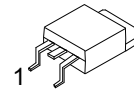
* High breakdown voltage



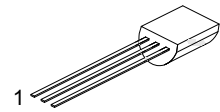
SOT-89



SOT-223



TO-252



TO-92

ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
08NM60L-AA3-R	08NM60G-AA3-R	SOT-223	G	D	S	Tape Reel
08NM60L-AB3-R	08NM60G-AB3-R	SOT-89	G	D	S	Tape Reel
08NM60L-TN3-R	08NM60G-TN3-R	TO-252	G	D	S	Tape Reel
08NM60L-T92-B	08NM60G-T92-B	TO-92	G	D	S	Tape Box
08NM60L-T92-K	08NM60G-T92-K	TO-92	G	D	S	Bulk

Note: Pin Assignment: G: Gate D: Drain S: Source

08NM60G-AA3-R	(1) R: Tape Reel, B: Tape Box, K: Bulk (2) AA3: SOT-223, AB3: SOT-89, TN3: TO-252 T92: TO-92 (3) G: Halogen Free and Lead Free, L: Lead Free
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MARKING

SOT-223	SOT-89
TO-252	TO-92

■ **ABSOLUTE MAXIMUM RATINGS** ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_{D}	0.8	A
	Pulsed (Note 2)	I_{DM}	3.2	A
Power Dissipation	SOT-223	P_{D}	3.8	W
	SOT-89		2	W
	TO-252		15	W
	TO-92		3	W
Junction Temperature		T_{J}	+150	$^{\circ}\text{C}$
Storage Temperature Range		T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	SOT-223	θ_{JA}	150	$^{\circ}\text{C/W}$
	SOT-89		180	
	TO-252		110	
	TO-92		160	
Junction to Case	SOT-223	θ_{JC}	32.8	$^{\circ}\text{C/W}$
	SOT-89		62.5	
	TO-252		8.3	
	TO-92		41.6	

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

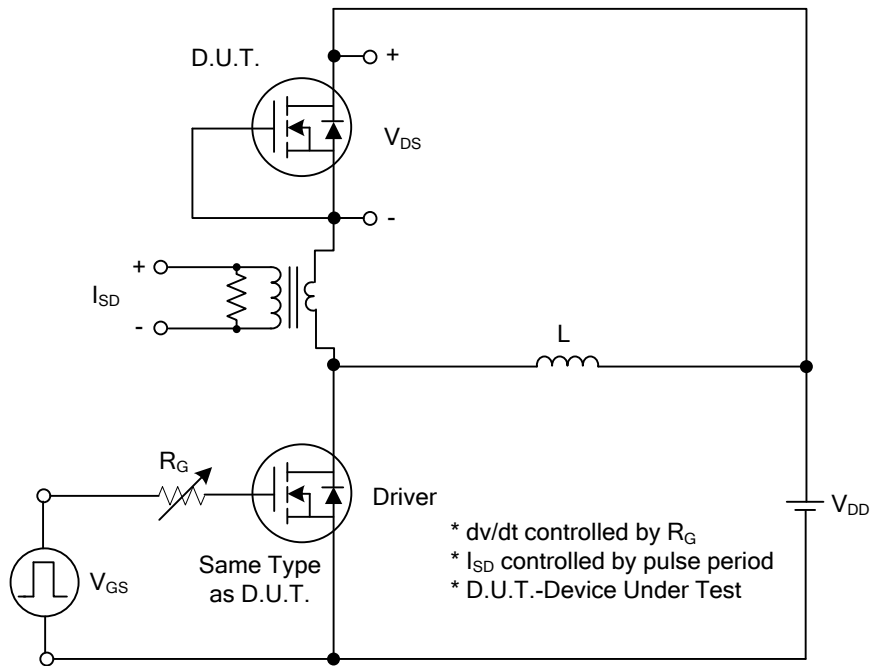
■ **ELECTRICAL CHARACTERISTICS** ($T_J=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =250μA, V _{GS} =0V	600			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =600V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} =+30V, V _{DS} =0V			+100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.5		4.5	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =0.4A			4.5	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =50V, f=1.0MHz		62		pF
Output Capacitance		C _{OSS}			23		pF
Reverse Transfer Capacitance		C _{RSS}			3.7		pF
SWITCHING PARAMETERS							
Total Gate Charge (Note 1)		Q _G	V _{DS} =480V, V _{GS} =10V, I _D =0.5A, (Note 1, 2)		12		nC
Gate to Source Charge		Q _{GS}			5		nC
Gate to Drain Charge		Q _{GD}			2.2		nC
Turn-ON Delay Time (Note 1)		t _{D(ON)}	V _{DS} =100V, V _{GS} =10V, I _D =0.5A, R _G =25Ω (Note 1, 2)		3.2		ns
Rise Time		t _R			18		ns
Turn-OFF Delay Time		t _{D(OFF)}			12		ns
Fall-Time		t _F			10		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				0.8	A
Maximum Body-Diode Pulsed Current		I _{SM}				3.2	A
Drain-Source Diode Forward Voltage (Note 1)		V _{SD}	I _S =0.8A, V _{GS} =0V			1.4	V
Reverse Recovery Time (Note 1)		t _{rr}	I _S =0.8A , V _{GS} =0V		120		ns
Reverse Recovery Charge		Q _{rr}	di/dt=100A/μs		260		nC

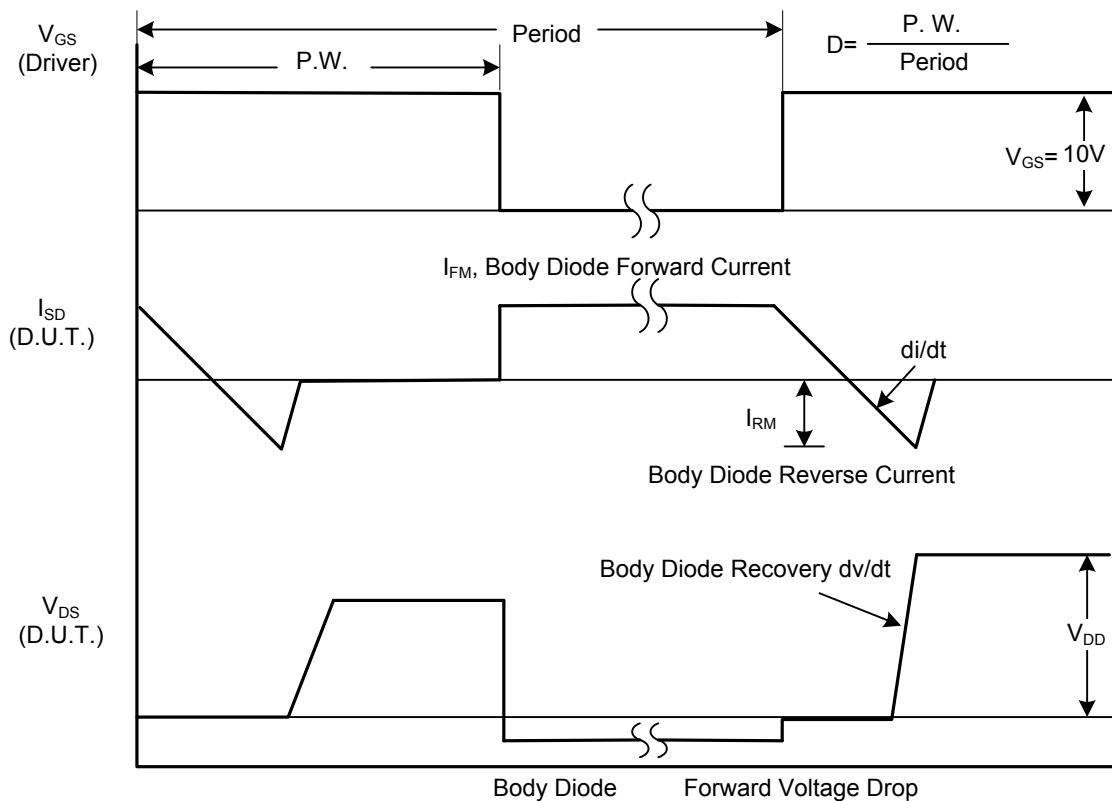
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

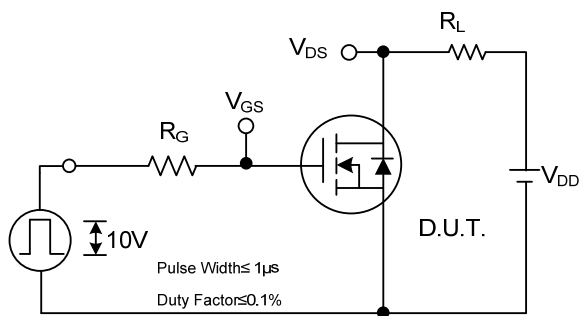


Peak Diode Recovery dv/dt Test Circuit

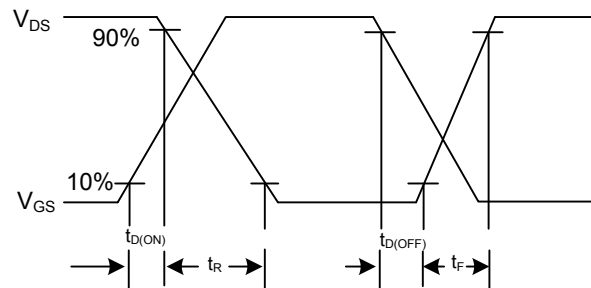


Peak Diode Recovery dv/dt Waveforms

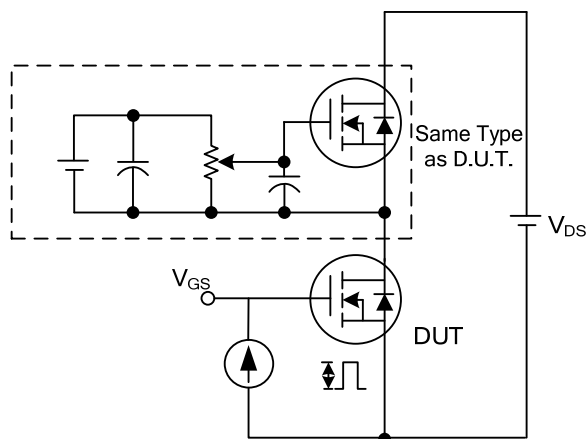
■ TEST CIRCUITS AND WAVEFORMS



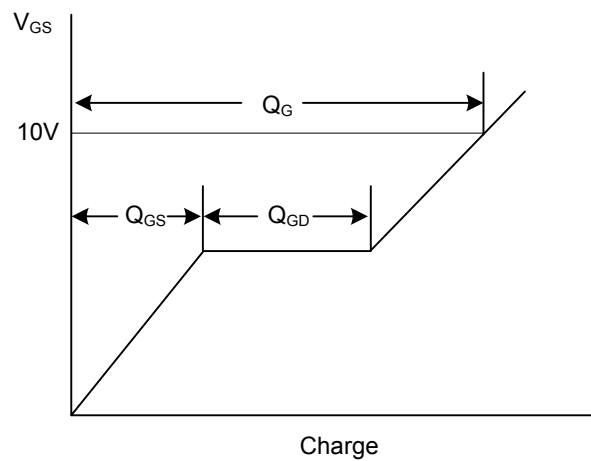
Switching Test Circuit



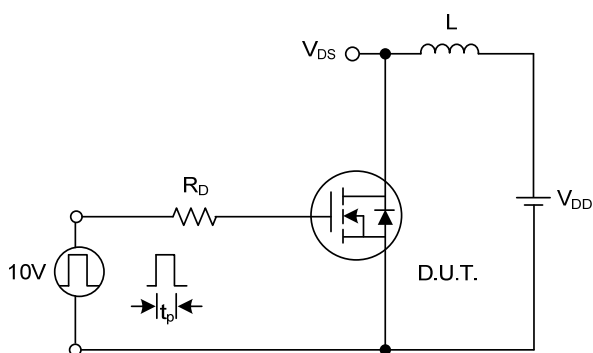
Switching Waveforms



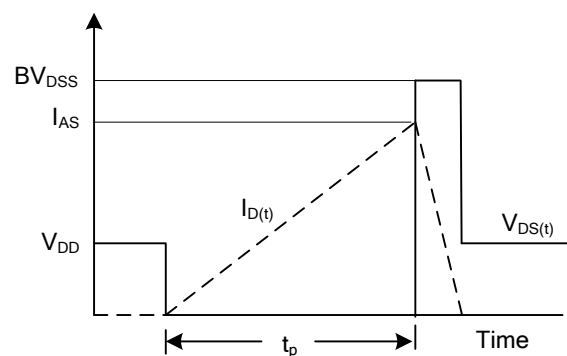
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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